

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	190	438/773.ccls.	US-PGPUB; USPAT	OR	OFF	2005/12/19 17:04
L3	4132	438/300.ccls. 438/305.ccls. 438/306.ccls. 438/307.ccls. 438/502.ccls. 438/509.ccls. 438/765.ccls. 438/769.ccls. 438/770.ccls. 438/773.ccls. 438/775.ccls.	US-PGPUB; USPAT	OR	OFF	2005/12/19 17:15
L4	22735	(box (buried near oxide) soi sos (silicon adj on adj insulator)) same epitax\$8	US-PGPUB; USPAT	OR	ON	2005/12/19 17:53
L5	453	L3 and L4	US-PGPUB; USPAT	OR	ON	2005/12/19 17:15
L6	22735	(box (buried near oxide) soi sos (silicon adj on adj insulator)) same epitax\$8	US-PGPUB; USPAT	OR	ON	2005/12/19 17:28
L7	73	L6 same ((silicon si semiconductor) near2 (oxygen near (rich dop\$6 implant\$6)))	US-PGPUB; USPAT	OR	ON	2005/12/19 17:28
L8	4132	438/300.ccls. 438/305.ccls. 438/306.ccls. 438/307.ccls. 438/502.ccls. 438/509.ccls. 438/765.ccls. 438/769.ccls. 438/770.ccls. 438/773.ccls. 438/775.ccls.	US-PGPUB; USPAT	OR	OFF	2005/12/19 17:31
L9	37	L8 and ((silicon si semiconductor) near2 (oxygen near (rich dop\$6 implant\$6)))	US-PGPUB; USPAT	OR	ON	2005/12/19 17:31
L10	97	(box (buried near oxide) soi sos (silicon adj on adj insulator)) and ((silicon si semiconductor) near2 (oxygen near (rich dop\$6 implant\$6)))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 17:32
L11	18	(silicon si semiconductor) near2 (oxygen near rich)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 17:34
L12	115	(silicon si semiconductor) near2 (oxygen near rich)	US-PGPUB; USPAT	OR	ON	2005/12/19 17:36
L13	18	("5223919" "5461243" "5714777" "5759898" "6077343").PN. OR ("6369438"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/19 17:39
L15	133	(silicon si semiconductor) near2 (oxygen near dop\$6)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 17:41

L16	16	L15 and (box (buried near oxide) soi sos (silicon adj on adj insulator))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/19 17:41
L17	336	(silicon si semiconductor) near2 (oxygen near dop\$6)	US-PGPUB; USPAT	OR	ON	2005/12/19 17:42
L18	76	L17 same ((box (buried near oxide) soi sos (silicon adj on adj insulator)) epitax\$8)	US-PGPUB; USPAT	OR	ON	2005/12/19 17:42
L19	348	(gate near (insulat\$6 dielectric oxide dioxide)) same ((native adj oxide) with (etch\$6 remov\$6))	US-PGPUB; USPAT	OR	ON	2005/12/19 17:45
L20	37	L19 same quality	US-PGPUB; USPAT	OR	ON	2005/12/19 17:45
L21	48	((elevated raised) near2 (source drain)) with (junction adj leakage)	US-PGPUB; USPAT	OR	ON	2005/12/19 17:48
L22	0	((box (buried near oxide) soi sos (silicon adj on adj insulator)) and epitax\$8 and ((silicon si semiconductor) near2 (oxygen near (dop\$6 rich))))).clm.	US-PGPUB	OR	ON	2005/12/19 17:56
L23	1	((box (buried near oxide) soi sos (silicon adj on adj insulator)) and epitax\$8 and ((silicon si semiconductor germanium ge) with (oxygen near4 (dop\$6 rich))))).clm.	US-PGPUB	OR	ON	2005/12/19 18:04
L24	19	((box (buried near oxide) soi sos (silicon adj on adj insulator)) and epitax\$8 and ((silicon si semiconductor germanium ge) with (oxygen near4 (dop\$6 rich implant\$8))))).clm.	US-PGPUB	OR	ON	2005/12/19 17:58
L25	17	(epitax\$8 and ((silicon si semiconductor germanium ge) with (oxygen near4 (dop\$6 rich))))).clm.	US-PGPUB	OR	ON	2005/12/19 18:04